

# N-Channel 250-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
250	0.220@ V <sub>GS</sub> = 10 V	14		
	0.260@ V <sub>GS</sub> = 4.5 V	13		

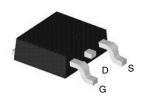
#### **FEATURES**

- Surface Mount
- Low-Profile Through-Hole
- Available in Tape and Reel
- Dynamic dV/dt Rating
- 150 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated

D

Compliant to RoHS Directive 2002/95/EC

**TO-252** Pin Configuration



Top View

GC S N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25$ °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	250	v			
Gate-Source Voltage	V <sub>GS</sub>	± 20				
Continuous Drain Current	$V_{GS}$ at 10 V $T_C = 25 \degree C$	- I <sub>D</sub> -	14			
	$V_{GS}$ at 10 V $T_C = 100 \text{ °C}$		10	А		
Pulsed Drain Current <sup>a, e</sup>	I <sub>DM</sub>	45	1			
Single Pulse Avalanche Energy <sup>b, e</sup>	E <sub>AS</sub>	380	mJ			
Avalanche Current <sup>a</sup>	I <sub>AR</sub>	10	А			
Repetiitive Avalanche Energy <sup>a</sup>		E <sub>AR</sub>	186	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	Pn	156	w		
	T <sub>A</sub> = 25 °C	гD	3.3			
Peak Diode Recovery dV/dt <sup>c, e</sup>		dV/dt	5.0	V/ns		
Operating Junction and Storage Temperature Rang	e	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C		
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>d</sup>	1 0		

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

- b.  $V_{DD} = 50 \text{ V}$ , starting  $T_J = 25 \text{ °C}$ , L = 2.7 mH,  $R_g = 25 \Omega$ ,  $I_{AS} = 12 \text{ A}$  (see fig. 12). c.  $I_{SD} \le 20 \text{ A}$ , dl/dt  $\le 150 \text{ A}/\mu\text{s}$ ,  $V_{DD} \le V_{DS}$ ,  $T_J \le 150 \text{ °C}$ .

d. 1.6 mm from case.



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THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	TYP.	MAX.	UNIT	
Maximum Junction-to-Ambient (PCB Mounted, Steady-State) <sup>a</sup>	R <sub>thJA</sub>	-	50	°C/W	
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	-	1.0		

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$	250	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1 \text{ mA}^c$	-	0.29	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zara Cata Valtaga Drain Current		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	10	
Durin Course Or Otato Desistance	P	$V_{GS} = 10 V I_D = 7 A$	-	220	300	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}$ I <sub>D</sub> = 5 A		260	390 mΩ	
Forward Transconductance	<b>g</b> <sub>fs</sub>	$V_{DS} = 50 \text{ V}, \text{ I}_{D} = 7 \text{ A}$	-	10	-	S
Dynamic						
Input Capacitance	C <sub>iss</sub>		-	735	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V, V_{DS} = 25 V$	-	130	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	10	-	
Total Gate Charge	Qg		-	15	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 125 \text{ V}, \text{ I}_{D} = 7 \text{ A}$	-	4	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	5	-	
Turn-On Delay Time	t <sub>d(on)</sub>		-	24	-	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 125 V, I <sub>D</sub> = 7 A, R <sub>g</sub> = 9.1 Ω	-	61	-	- ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	45	-	
Fall Time	t <sub>f</sub>		-	39	-	
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	I <sub>S</sub>	Maximum Body-Diode Continuous Current	-	-	14	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>	Maximum Body-Diode Pulsed Current	-	-	45	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V		-	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>		-	150	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 14 \text{ A}, \text{ dI/dt} = 100 \text{ A}/\mu \text{s}, \text{ V}_{\text{DS}} = 100 \text{ V}$		1.4	-	μC

#### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

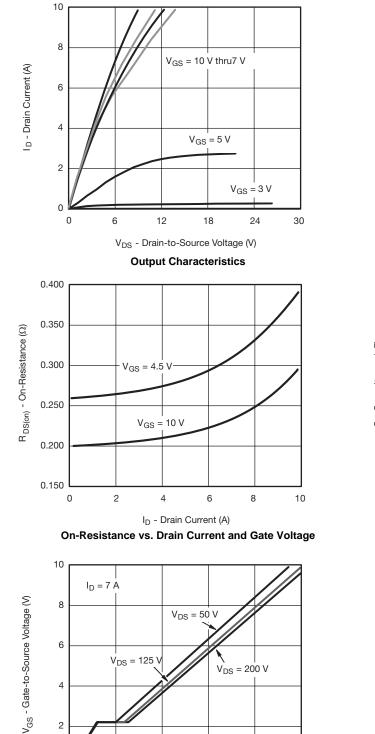
b. Pulse width  $\leq$  300 µs; duty cycle  $\leq$  2 %.

c. Uses IRF640/SiHF640 data and test conditions.



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V<sub>DS</sub> = 125 V

3

6

Qg - Total Gate Charge (nC)

**Gate Charge** 

9

4

2

0

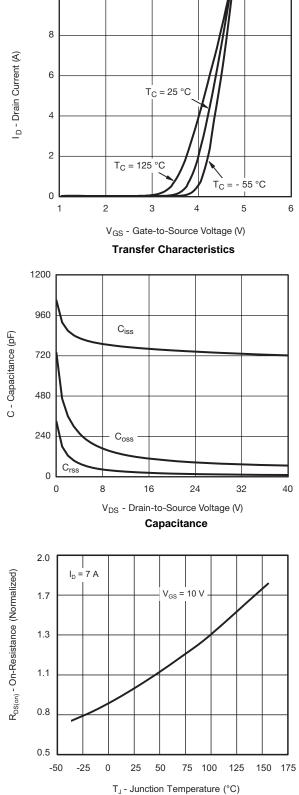
0

V<sub>DS</sub> = 200 V

12

15

#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

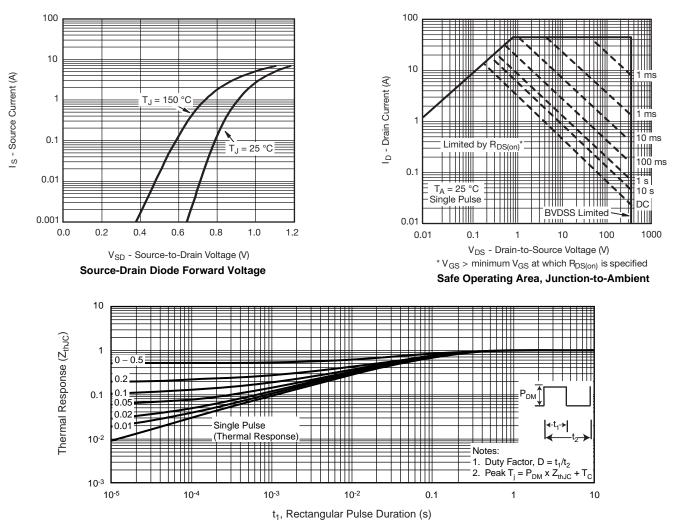


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**On-Resistance vs. Junction Temperature** 

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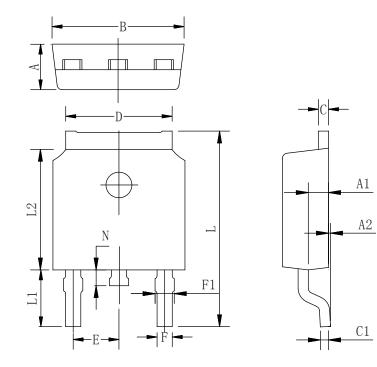
### N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Maximum Effective Transient Thermal Impedance, Junction-to-Case

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# TO-252-2L PACKAGE OUTLINE



#### COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
А	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	

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